Sensitive Gate Triacs Series

Silicon Bidirectional Thyristors

Designed for use in solid state relays, MPU interface, TTL logic and any other light industrial or consumer application. Supplied in an inexpensive TO-92 package which is readily adaptable for use in automatic insertion equipment.

Features

- One-Piece, Injection-Molded Package
- Blocking Voltage to 600 V
- Sensitive Gate Triggering in Four Trigger Modes (Quadrants) for all possible Combinations of Trigger Sources, and especially for Circuits that Source Gate Drives
- All Diffused and Glassivated Junctions for Maximum Uniformity of Parameters and Reliability
- Improved Noise Immunity (dv/dt Minimum of 10 V/µsec at 110°C)
- Commutating di/dt of 1.6 A/msec at 110°C
- High Surge Current of 8 A
- These are Pb–Free Devices

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage $(T_J = -40 \text{ to } +125^{\circ}\text{C})^{(1)}$ Sine Wave 50 to 60 Hz, Gate Open	V _{DRM,} V _{RRM}	600	V
On-State RMS Current Full Cycle Sine Wave 50 to 60 Hz $(T_{C} = 50^{\circ}C)$	I _{T(RMS)}	1.0	A
Peak Non-Repetitive Surge Current One Full Cycle, Sine Wave 60 Hz $(T_C = 110^{\circ}C)$	I _{TSM}	8.0	A
Circuit Fusing Considerations (t = 8.3 ms)	l ² t	0.35	A ² s
Average Gate Power (T _C = 80°C, t \leq 8.3 ms)	P _{G(AV)}	1.0	W
Peak Gate Current (t \leq 20 µs, T _J = +125°C)	I _{GM}	1.0	Α
Operating Junction Temperature Range	ТJ	–40 to +125	°C
Storage Temperature Range	T _{stg}	–40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



ON Semiconductor

http://onsemi.com



PIN ASSIGNMENT				
1	Main Terminal 1			
2	Gate			
3	Main Terminal 2			

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ extsf{ heta}JC}$	50	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{ hetaJA}$	160	°C/W
Maximum Lead Temperature for Soldering Purposes for 10 Seconds	ΤL	260	°C

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS				•	
$ \begin{array}{ll} \mbox{Peak Repetitive Blocking Current} & T_J = 25^\circ C \\ \mbox{(V}_D = Rated V_{DRM}, V_{RRM}; \mbox{Gate Open)} & T_J = +125^\circ C \\ \end{array} $	I _{DRM} , I _{RRM}	-		5.0 500	μA
ON CHARACTERISTICS					
Peak On–State Voltage (I _{TM} = \pm 1.4 A Peak; Pulse Width \leq 2.0 ms, Duty Cycle \leq 2.0%)	V _{TM}	-	-	1.56	V
$ \begin{array}{l} \mbox{Gate Trigger Current (Continuous dc)} \\ (V_D = 12 \mbox{ Vdc, } R_L = 30 \ \Omega) \\ \mbox{ MT2(+), } G(+) \\ \mbox{ MT2(+), } G(-) \\ \mbox{ MT2(-), } G(-) \\ \mbox{ MT2(-), } G(+) \\ \end{array} $	I _{GT}	0.15 0.15 0.15 0.25	- - -	5.0 5.0 5.0 7.0	mA
Latching Current (V_D = 12 V, I_G = 1.2 x I_{GT}) MT2(+), G(+) All Types MT2(+), G(-) All Types MT2(-), G(-) All Types MT2(-), G(+) All Types	ΙL	- - -	- - -	10 20 10 10	mA
Gate Trigger Voltage (Continuous dc) $(V_D = 12 \text{ Vdc}, R_L = 30 \Omega)$ MT2(+), G(+) All Types MT2(-), G(-) All Types MT2(-), G(-) All Types MT2(-), G(+) All Types	V _{GT}	- - -	- - -	1.3 1.3 1.3 1.3	V
Gate Non–Trigger Voltage (V_D = 12 V, R_L = 30 Ω , T_J = 125°C) All Four Quadrants	V _{GD}	0.2	_	1.3	V
Holding Current ($V_D = 12$ Vdc, Initiating Current = 50 mA, Gate Open)	Ι _Η	-	-	10	mA
DYNAMIC CHARACTERISTICS					
Rate of Change of Commutating Current ($V_D = 400 \text{ V}, I_{TM} = 0.84 \text{ A}, \text{ Commutating dv/dt} = 1.5 \text{ V/}\mu\text{s}, \text{ Gate Open}, T_J = 110^{\circ}\text{C}, f = 250 \text{ Hz}, \text{ with Snubber}$)	di/dt(c)	1.6	_	-	A/ms
Critical Rate of Rise of Off–State Voltage ($V_D = 67\%$ Rated V_{DRM} , Exponential Waveform, Gate Open, $T_J = 110^{\circ}$ C)	dv/dt	20	60	-	V/µs
Repetitive Critical Rate of Rise of On–State Current, T_J = 125°C Pulse Width = 20 µs, IPK _{max} = 15 A, diG/dt = 1 A/µs, f = 60 Hz	di/dt	-	-	20	A/μs

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V _{DRM}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
Ι _Η	Holding Current





Quadrant Definitions for a Triac

All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.







Figure 4. On-State Characteristics





Figure 6. Maximum Allowable Surge Current







Figure 9. Typical Latching Current versus Junction Temperature



Figure 8. Typical Gate Trigger Voltage versus Junction Temperature







Note: Component values are for verification of rated (di/dt)c. See AN1048 for additional information.

Figure 11. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)c

ORDERING & SHIPPING INFORMATION: Packaging Options, Device Suffix

U.S.	Europe Equivalent	Shipping [†]	Description of TO–92 Tape Orientation
	Z0107MARL1G	Radial Tape and Reel (2K/Reel)	Flat side of TO-92 and adhesive tape visible
Z0107MAG		Bulk in Box (5K/Box)	N/A, Bulk
Z0107MARLRPG		Radial Tape and Fan Fold Box (2K/Box)	Round side of TO-92 and adhesive tape visible
Z0107MARLRFG		Radial Tape and Fan Fold Box (2K/Box)	Round side of TO-92 and adhesive tape on re- verse side

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

PACKAGE DIMENSIONS

TO-92 (TO-226AA) CASE 029-11 ISSUE AM



ON Semiconductor and IIIII are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death agsociated with such unintended or unauthorized use payers and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death agsociated with such unintended or unauthorized use ports and set and performance of the part. SCILLC is an Equal Opportunit//Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional informa Sales Representative

For additional information, please contact your local Sales Representative